



SEMITRANS® 3

Trench IGBT Modules

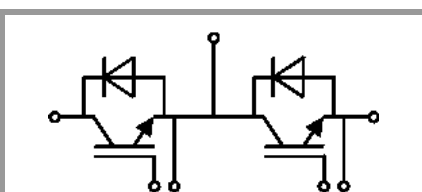
SKM400GB126D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 150 °C	T _c = 25 °C	470	A
		T _c = 80 °C	327	A
I _{Cnom}			300	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		600	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 600 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 125 °C	10	μs
T _j			-40 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	352	A
		T _c = 80 °C	240	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		600	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		2844	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}			500	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 300 A	T _j = 25 °C		1.69	2.10	V
	V _{GE} = 15 V chipelevel	T _j = 125 °C		2.01	2.45	V
V _{CE0}	chipelevel	T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V chipelevel	T _j = 25 °C		2.3	3	mΩ
		T _j = 125 °C		3.7	4.5	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 12 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C			4	mA
	V _{CE} = 1200 V	T _j = 125 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		21.4		nF
C _{oes}		f = 1 MHz		1.12		nF
C _{res}		f = 1 MHz		0.97		nF
Q _G	V _{GE} = - 8 V...+ 20 V			2800		nC
R _{Gint}	T _j = 25 °C			2.5		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C		330		ns
t _r	I _C = 300 A	T _j = 125 °C		50		ns
E _{on}	V _{GE} = +15/-15 V	T _j = 125 °C		29		mJ
t _{d(off)}	R _{G on} = 2 Ω	T _j = 125 °C		650		ns
t _f	R _{G off} = 2 Ω	T _j = 125 °C		110		ns
E _{off}		T _j = 125 °C		48		mJ
R _{th(j-c)}	per IGBT				0.08	K/W



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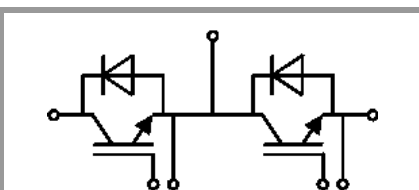
Features

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- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$
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Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		1.60	1.80	V
	V _{GE} = 0 V	T _j = 125 °C		1.60	1.80	V
	chiplevel					
V _{F0}		T _j = 25 °C		1	1.1	V
	chiplevel	T _j = 125 °C		0.8	0.9	V
r _F		T _j = 25 °C		2.00	2.3	mΩ
	chiplevel	T _j = 125 °C		2.7	3	mΩ
I _{RRM}	I _F = 300 A	T _j = 125 °C		390		A
Q _{rr}	di/dt _{off} = 6300 A/μs	T _j = 125 °C		77		μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C		27		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.18	K/W
Module						
L _{CE}				15		nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.35		mΩ
		T _C = 125 °C		0.5		mΩ
R _{th(c-s)}	per module			0.02	0.038	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



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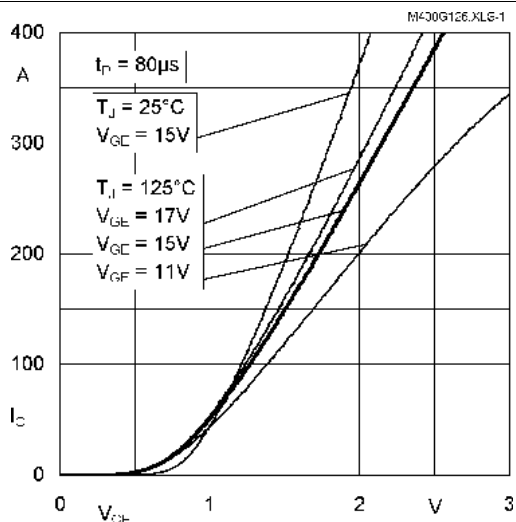


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

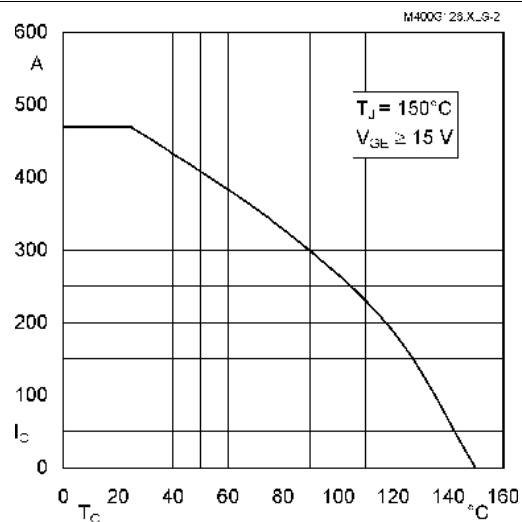


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

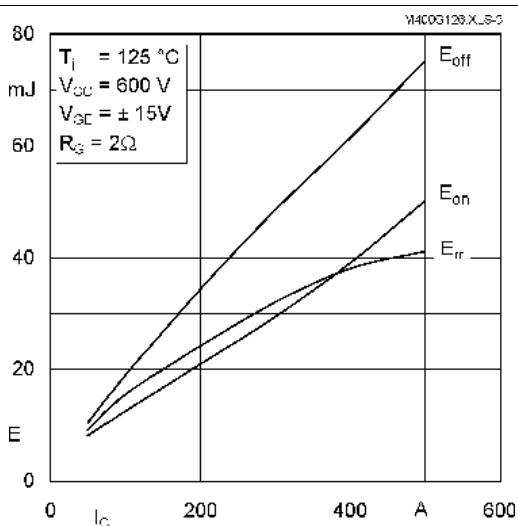


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

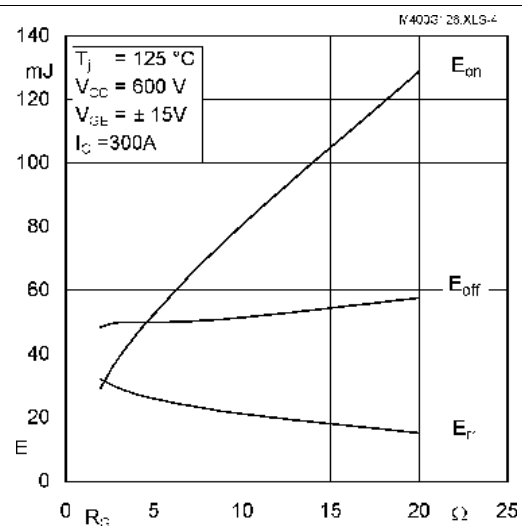


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

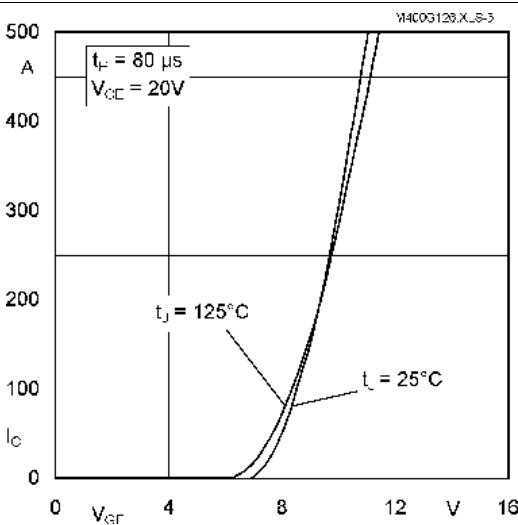


Fig. 5: Typ. transfer characteristic

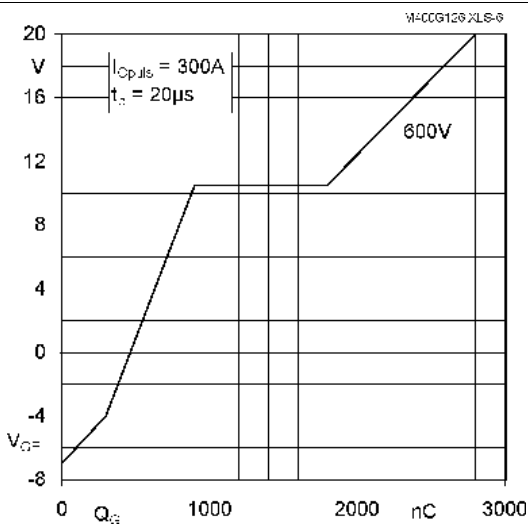
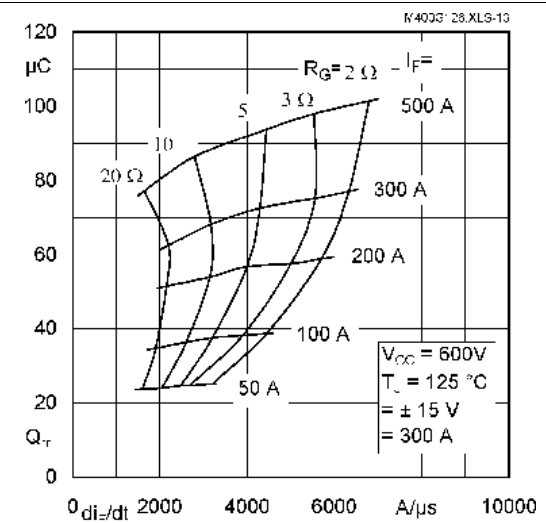
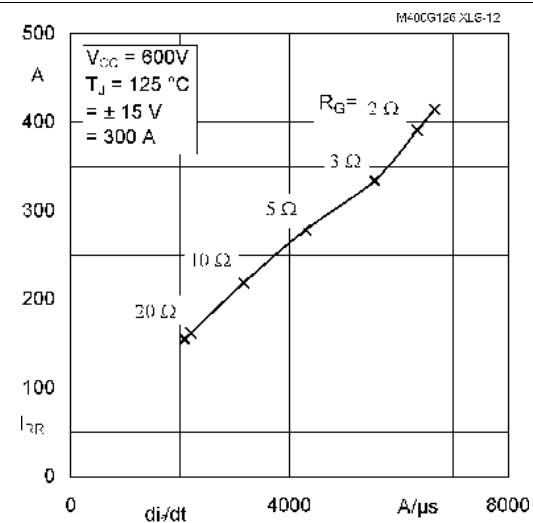
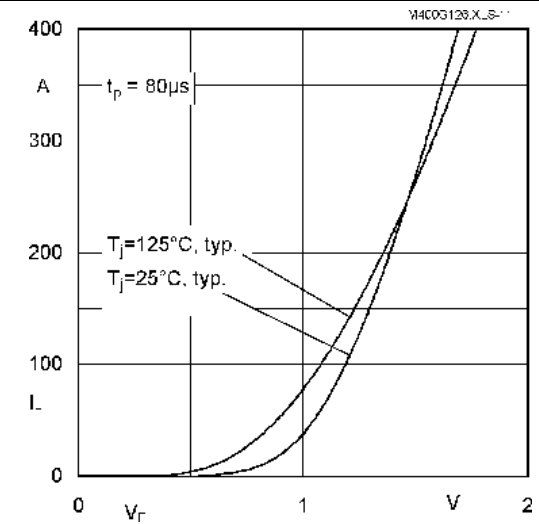
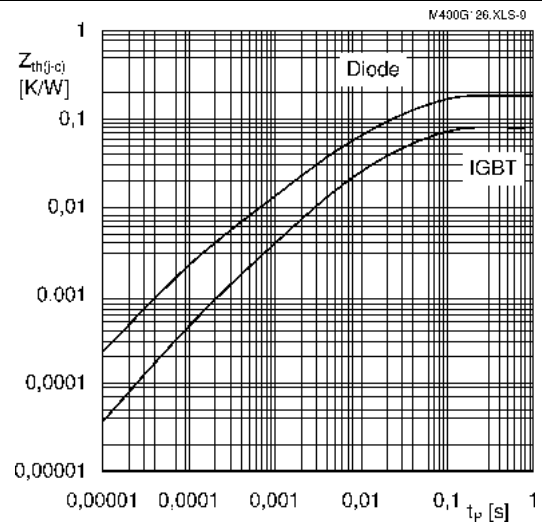
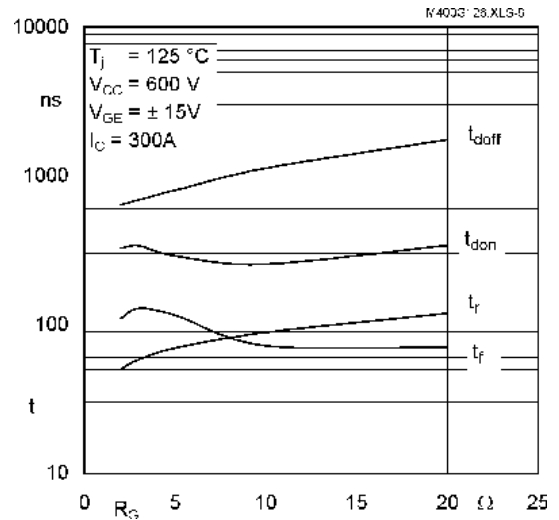
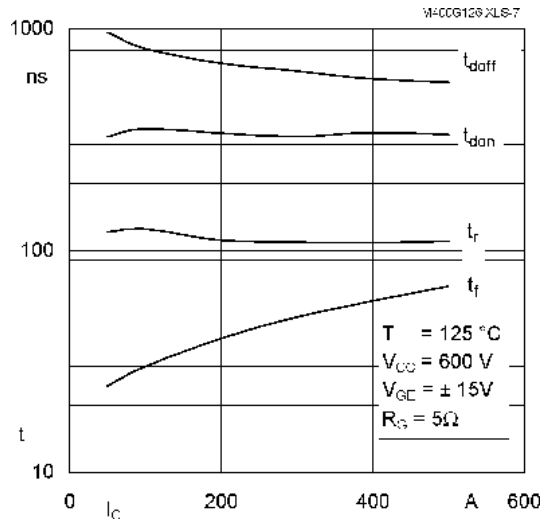
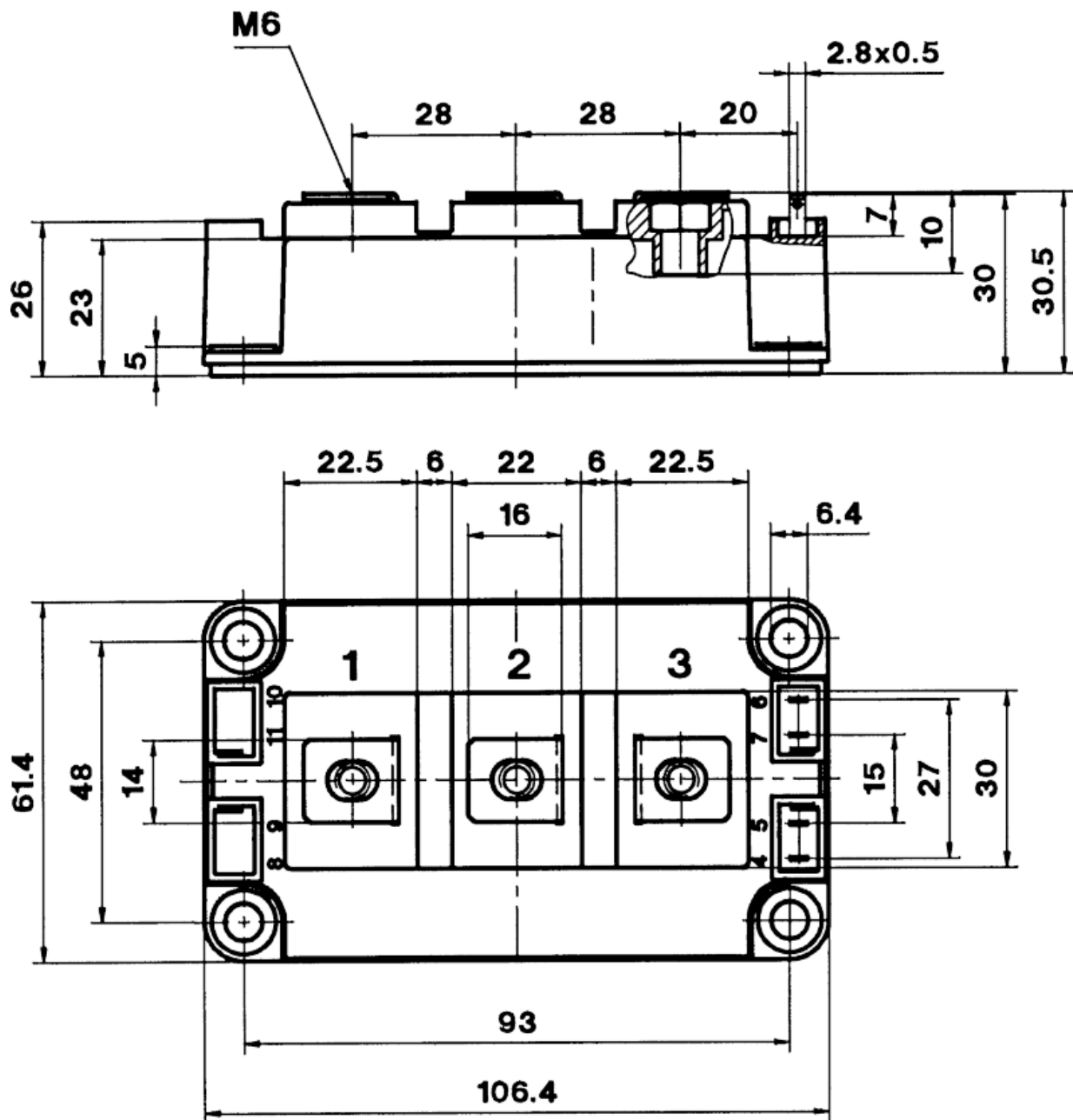
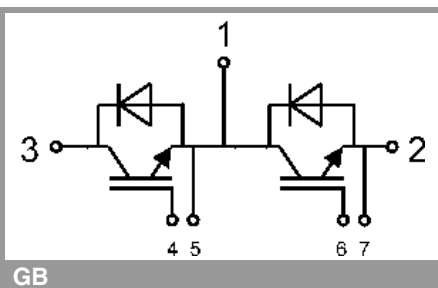


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.